

Single-supply voltage-output temperature sensor in bare die form

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Description

The SiS60A measures temperature over a wide -60°C to 125°C range. The device operates from a single supply and provides a linear voltage output with temperature coefficient of 6.25mV/°C. By design DC offset of +424 mV permits measurement of negative temperature without need for negative supply. Nominal output range is within 49mV (-60°C) and 1205mV (125°C). Output precision is calibrated on-die to $\pm 2\%$ max at 25°C and $\pm 4\%$ max over the full range. 2.7V operation & 125µA max consumption enable logic gate outputs to power this device, which combines intrinsic shutdown capability with simplified integration.

Ordering Information

The following part suffixes apply:

- No suffix MIL-STD-883 /2010B Visual Inspection
- "H" MIL-STD-883 /2010B Visual Inspection + MIL-PRF-38534 Class H LAT
- "K" MIL-STD-883 /2010A Visual Inspection (Space)
 + MIL-PRF-38534 Class K AT

LAT = Lot Acceptance Test.

For further information on LAT process flows see below.

www.siliconsupplies.com\quality\bare-die-lot-qualification

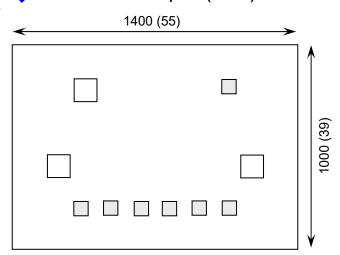
Supply Formats:

- Default Die in Waffle Pack (400 per tray capacity)
- Sawn Wafer on Tape On request
- Unsawn Wafer On request
- Die Thickness <> 350µm(14 Mils) On request
- Assembled into Ceramic Package On request

Features:

- Wide temperature range: -60 to +12°C
- Single-supply range: 2.7-10V
- ±1% typical accuracy at 25%
- ±2% typical accuracy of er -60 to +125°C range
- Low supply current: 125uA maximum
- Minimal self-heating: >= 0.1°C in still air
- ESD rated to 2k + BN

Die Dimensions in µm (mils)



Mechanical Specification

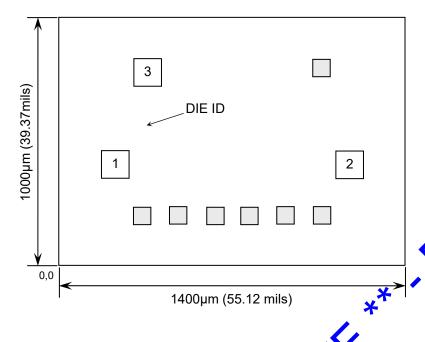
Die Size (Unsawn)	1400 x 1000 55 x 39	μm mils	
Minimum Bond Pad Size	112 x 112 4.4 x 4.4	μm mils	
Die Thickness	350 (±20) 13.78 (±0.79)	μm mils	
Top Metal Composition	Al 1%Si 1.1μm		
Back Metal Composition	N/A – Bare Si		





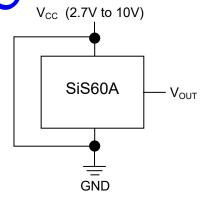
Pad Layout and Functions

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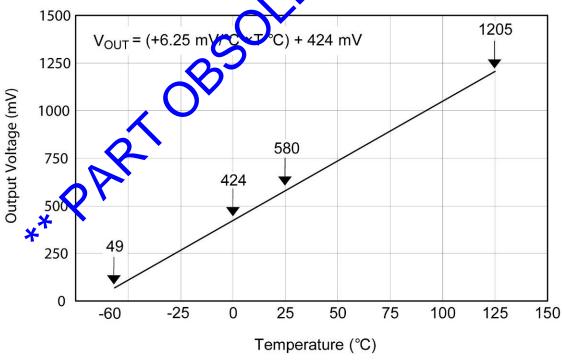


PAD	FUNCTION	COORDINA	TES (μm)	
1 AD 1 ONOTION	Х	Υ		
1	V _{CC}	174.5	350	
2	V _{OUT}	1124	350	
3	GND	300	724	
CONNECT OHIP BACK TO GND				

Simplified Schematic



Output Voltage versus Temperature







Absolute Maximum Ratings¹

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PARAMETER	SYMBOL	VALUE	UNIT
DC Supply Voltage Range	V _{CC}	-0.2 to +12	
Output Voltage	V _{OUT}	-0.6 to V _{CC} +0.6	V
Load Current	I _{LOAD}	10	ΜA
Input Current (Any pin)	I _{IN}	5	mA
Storage Temperature	T _{STG}	-65 to +150	°C
Operating Junction Temperature	T _J	-60 to +125	°C
Thermal Resistance ²	R _{eJA}	162	°C/W
Electrostatic Discharge (HBM)	V _{ESD}	2	kV

^{1.} Operation above the absolute maximum rating may cause device failure. Operation at the absolute maximum ratings, for extended periods, may reduce device reliability. 2. Die assembled in TO-92 package in still air.

Recommended Operating Conditions

PARAMETER	SYMBOL	MIN	MAX	UNITS
DC Supply Voltage	V _{CC}	2.7	10	V
Load Current	I _{LOAD}	- *	1	μA
Operating Temperature	T _A	-6	+125	°C

DC Electrical Characteristics (V_{CC} = V, V_{CC} = 1µA , T_J = T_A = 25°C unless otherwise specified)

DADAMETED	SYMBOL	CONDITIONS	LIMITS			LIMITO	
PARAMETER	STIVIBUL	CONDITIONS	MIN	TYP	MAX	UNITS	
Accuracy	ΔΤ ₁	$T_A = Y_J = 25^{\circ}C$	-2	±1	+2	°C	
		$T_A = Y_J = Full Range$	-4	±2	+4		
Output Voltage	V _{OUT}	0°C	-	424	-	mV	
Non-linearity	-0	-	-0.8	-	+0.8	°C	
Sensor Gain		$T_A = T_J = Full Range$	6.00	6.25	6.50	mV/°C	
Output Impedance	. Роит	T _A = T _J = Full Range	-	-	800	Ω	
		$3V \le +V_{CC} \le 10V$,	-0.3	-	0.3	mV/V	
Line Regulation	ΔV _{OUT}	$T_A = T_J = Full Range$	0.0				
	•	$2.7V \le +V_{CC} \le 3.3V$, $T_A = T_J = Full Range$	-3	-	3	mV	
Quiescent Current	Icc	$2.7V \le +V_{CC} \le 10 \text{ V},$	-	82	110	μА	
		$T_A = T_J = 25$ °C					
		$2.7V \le +V_{CC} \le 10 \text{ V},$	-	-	125		
		$T_A = T_J = Full Range$					
Quiescent Current Change	Δl _{CC}	$2.7V \le +V_{CC} \le 10 \text{ V}$	-	5	-	μA	
Temperature				0.0		A /9.0	
coefficient of Quiescent current	-	-	-	0.2	-	μΑ/°C	
Long-term stability	-	$T_J = T_{MAX} = 125$ °C for 1000 hours	-	±0.2	-	°C	





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Typical Characteristics (V_{CC} =3V, I_{LOAD} = 1 μA , T_J = T_A = 25°C unless otherwise specified)

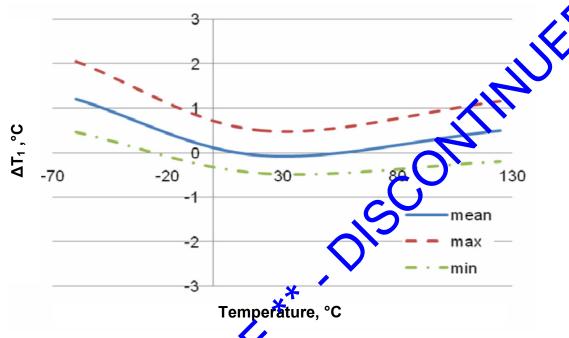
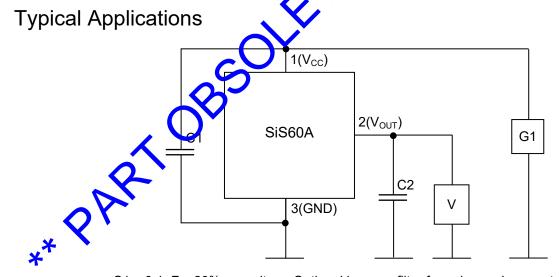


FIGURE 1. Tempera ure measurement accuracy



 $C1 - 0.1 \mu F \pm 20\%$ capacitor – Optional by-pass filter for noisy environments

C2 – 1µF ± 20% capacitor – Optional 199-Hz low-pass filter for noisy environments

G1 - DC supply 2.7V - 10V

V - Voltmeter

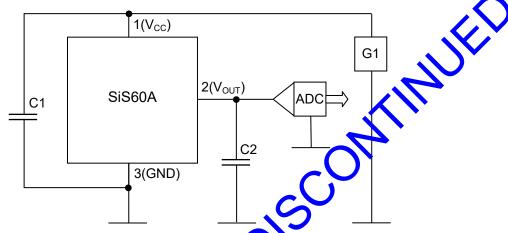
FIGURE 2. Output with noise reduction circuit





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Typical Applications continued



C1 – 0.1µF ± 20% capacitor – Optional by-pass (ter pr hoisy environments

C2 – 1µF ± 20% capacitor – Optional 199-Hz low-ps filter for noisy environments

G1 – DC supply 2.7V - 10V

ADC - Analog to Digital Converter

FIGURE 3. Output to ADC with noise reduction circuit

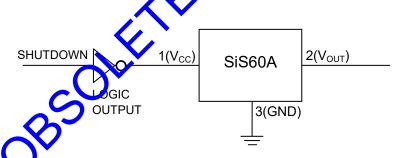


FIGURE 6. Logic device drive with intrinsic shutdown

Formulae

Linear Transfer Function

 V_{OUT} (6.25mV/°C×T°C) +424mV

Where:

- T = Temperature
- V_{OUT} = SiS60A output voltage.

Die Self-Heating Calculation

$$T_{J} = T_{A} + R_{\theta JA} \left[\left(V_{CC} I_{CC} \right) + \left(V_{CC} - V_{OUT} \right) I_{LOAD} \right]$$

Where:

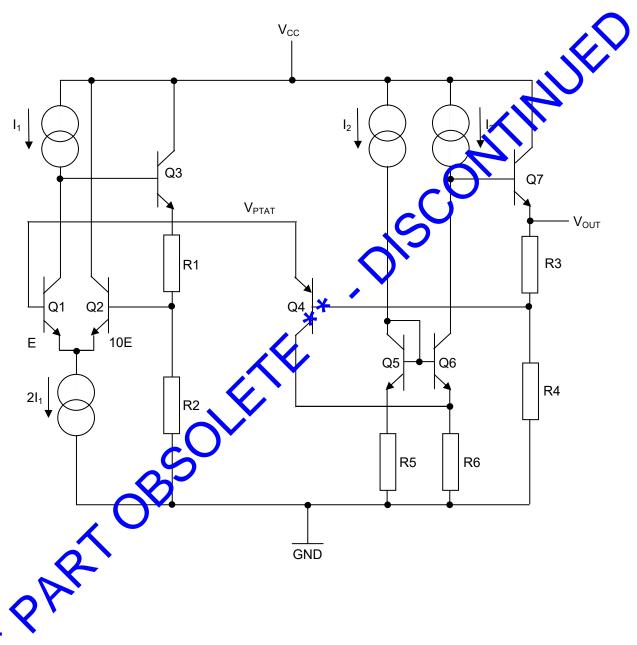
- I_{CC} = SiS60A quiescent current
- I_{LOAD} = The load current on the SiS60A output





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Block Diagram



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